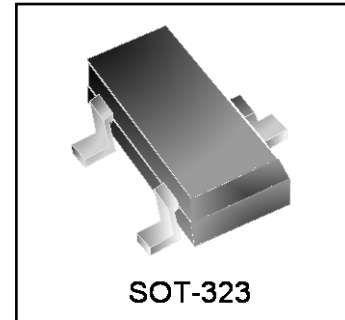
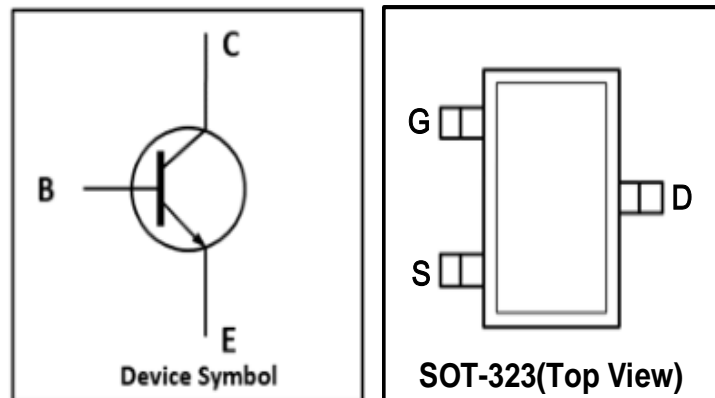


**NPN Silicon Transistor**
**Features**

- Ideally suited for automatic insertion
- For switching and AF amplifier applications

**Mechanical Characteristics**

- SOT-323 package
- Marking : Making Code
- RoHS Compliant


**Schematic & PIN Configuration**

**Absolute Maximum Rating**

Parameter	Symbol	Value	Unit
Collector Base Voltage	$V_{CBO}$	50	V
Collector Emitter Voltage	$V_{CEO}$	45	V
Emitter Base Voltage	$V_{EBO}$	6	V
Collector Current	$I_C$	0.1	A
Collector Power Dissipation	$P_C$	200	mW
Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	-55 ~ +150	°C

Electrical Characteristics ( $T_{amb}=25^{\circ}C$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10\mu A, I_E = 0$	50	-	-	V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10mA, I_B = 0$	45	-	-	V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	6	-	-	V
Collector cut-off current	$I_{CBO}$	$V_{CB} = 30V, I_E = 0$	-	-	15	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 5V, I_C = 0$	-	-	100	nA
DC current gain	$h_{FE}$	$V_{CE} = 5V, I_C = 2mA$	200	-	450	-
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 100mA, I_B = 5mA$	-	-	0.6	V
		$I_C = 10mA, I_B = 0.5mA$	-	-	0.25	
Base-emitter voltage	$V_{BE}$	$V_{CE}=5V, I_C = 10mA$	-	-	0.77	V
		$V_{CE}=5V, I_C = 2mA$	0.58	-	0.7	
Transition frequency	$f_T$	$V_{CE}=5V, I_C=10mA, f=100MHz$	100	-	-	MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = 10V, I_E = 0, f = 1MHz$	-	-	4.5	pF

Typical Characteristics

Figure 1. Static Characteristics

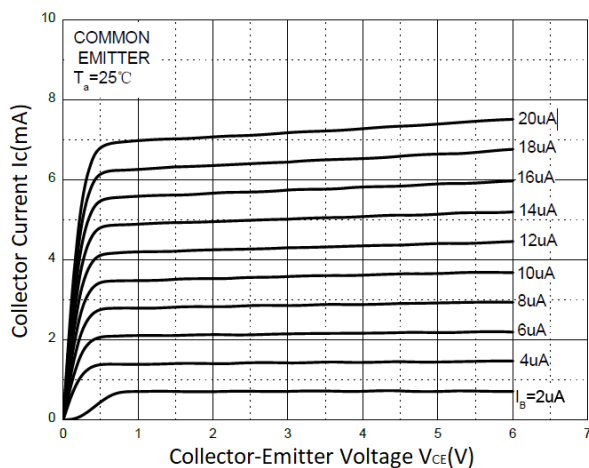


Figure 2.  $h_{FE}$  vs.  $I_C$

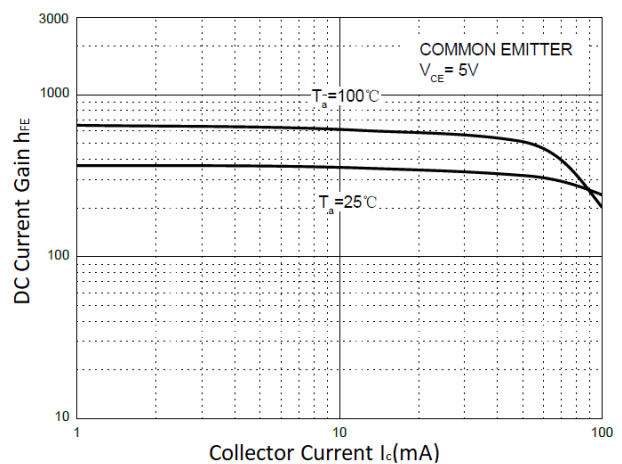


Figure 3.  $V_{BE(sat)}$  vs.  $I_c$

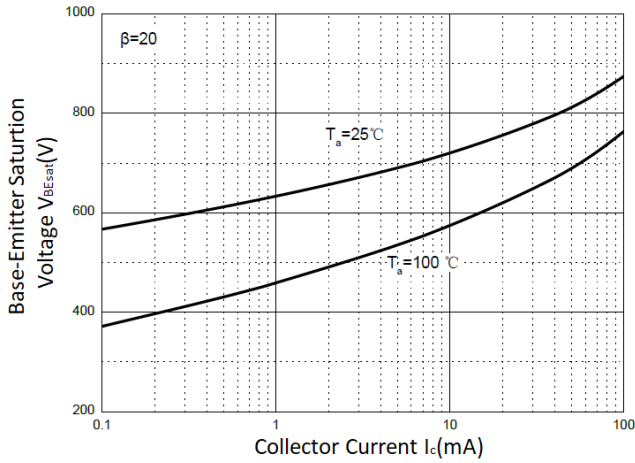


Figure 4.  $V_{CE(sat)}$  vs.  $I_c$

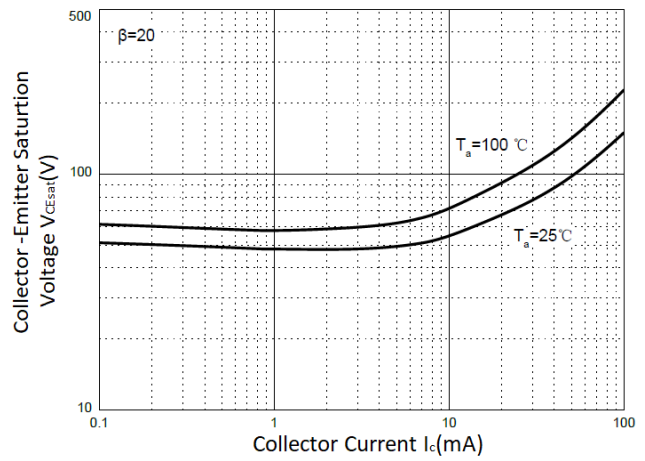


Figure 5.  $I_c$  vs.  $V_{BE}$

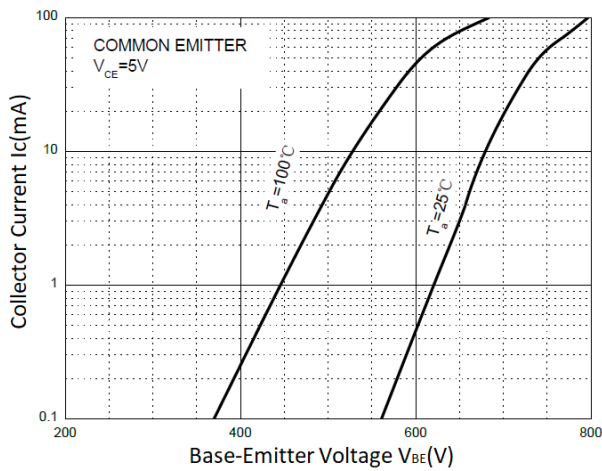


Figure 6.  $f_T$  vs.  $I_c$

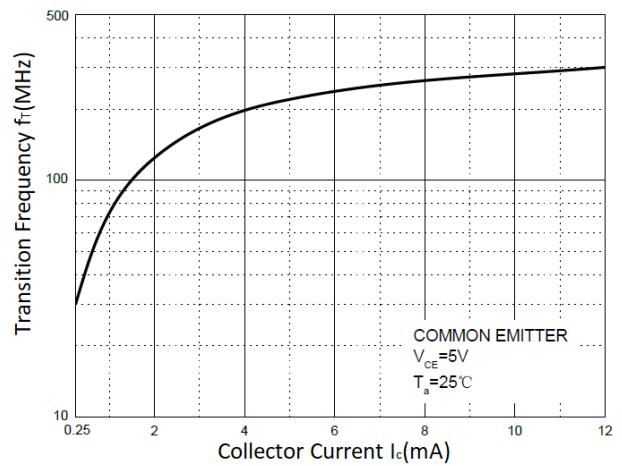


Figure 7.  $C_{ob} / C_{ib}$  vs.  $V_{CB} / V_{EB}$

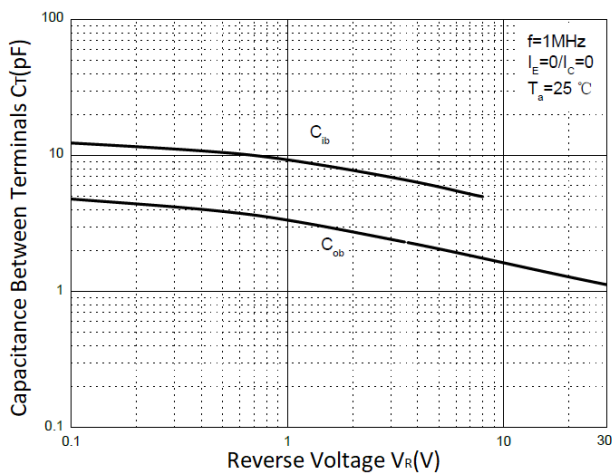
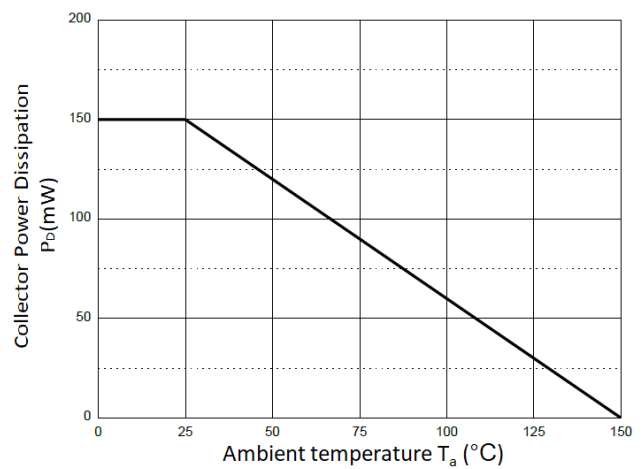


Figure 8.  $P_c$  vs.  $T_a$



Outline Drawing – SOT-323

### PACKAGE OUTLINE

**SOT-323**

SYMBOL	MILLIMETER		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
D	2.000	2.200	0.079	0.087
b	0.300	0.500	0.012	0.020
c	0.100	0.150	0.004	0.006
E	2.150	2.450	0.085	0.096
E1	1.150	1.350	0.045	0.053
e	0.650TYP		0.026TYP	
L	0.525 REF		0.021 REF	
θ	0	8°	0	8°

DIMENSIONS		
DIM	INCHES	MILLIMETERS
M	0.076	1.90
C	0.036	0.9
Z	0.108	2.7
e	0.026	0.65
e1	0.052	1.30
b	0.028	0.7

**Notes**

1. Dimensioning and tolerances per ANSI Y14.5M, 1985.
2. Controlling Dimension: Inches
3. Pin 3 is the cathode (Unidirectional Only).
4. Dimensions are exclusive of mold flash and metal burrs.

Marking Codes

Part Number	WT847BW
Marking Code	1F

Package Information

Qty: 3k/Reel

CONTACT INFORMATION

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WAYON website: <http://www.way-on.com>

For additional information, please contact your local Sales Representative.

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Specifications are subject to change without notice.  
The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time.  
Users should verify actual device performance in their specific applications.

单击下面可查看定价，库存，交付和生命周期等信息

[>>WAY-ON\(维安\)](#)